





**SN74HCS573** SCLS876A - OCTOBER 2021 - REVISED DECEMBER 2022

# SN74HCS573 Octal Transparent D-Type Latches with Schmitt-Trigger Inputs, 3-State **Outputs, and Flow-Through Pinout**

## 1 Features

TEXAS

INSTRUMENTS

- Wide operating voltage range: 2 V to 6 V
- Schmitt-trigger inputs allow for slow or noisy input signals
- Low power consumption
  - Typical I<sub>CC</sub> of 100 nA
  - Typical input leakage current of ±100 nA
  - ±7.8-mA output drive at 6 V
- Extended ambient temperature range: -40°C to +125°C, T<sub>A</sub>

# 2 Applications

- Parallel data storage
- Digital bus buffer

# **3 Description**

The SN74HCS573 contains eight D-type latches. All inputs include Schmitt-trigger architecture. All channels share a latch enable (LE) input and output enable  $(\overline{OE})$  input. This device has a flow-through pinout which allows for easier bus routing.

#### **Device Information**

PART NUMBER	PACKAGE <sup>(1)</sup>	BODY SIZE (NOM)					
SN74HCS573	RKS (VQFN, 20)	4.50 mm × 2.50 mm					
	DGS (VSSOP, 20)	5.10 mm × 3.00 mm					

For all available packages, see the orderable addendum at (1) the end of the data sheet.

	Low Power	Noise Rejection	Supports Slow Inputs
Input Voltage Waveforms	Input Voltage	tinden Time	and tindul Time
Standard CMOS Input Response Waveforms	Supply Current Input Voltage	Output Voltage	Output Current Voltage
Schmitt-trigger CMOS Input Response Waveforms	Adding Input Voltage	Output Ourrent Voltage	Output Current Voltage

## Benefits of Schmitt-trigger inputs





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# **4 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

C	hanges from Revision * (October 2021) to Revision A (December 2022)	Page
•	Changed from Application Information to Production Data	1
•	Added DGS device to Device Information Table	1
•	Added DGS (SSOP) Package Information	3
•	Added DGS package Thermal Information	4
•	Updated the Detailed Design Procedure section	13



ŌĒ

1D 2

2D

3D 4

4D 5

5D

6D 7

7D 8

8D 🧕

3)

6

VCC

(<u>19</u> 1Q

(<u>18</u> 2Q

(17 3Q

:16

(15

(14 6Q

(<u>13</u> 7Q

(12 8Q

LE

4Q

5Q

1 20

PAD

10 11

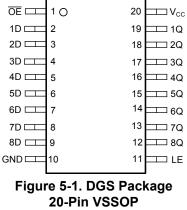
Figure 5-2. RKS Package

20-Pin VQFN

**Top View** 

GND

## **5** Pin Configuration and Functions



Top View

## **Pin Functions**

	PIN	I/O	DESCRIPTION			
NAME	NO.	- 1/0	DESCRIPTION			
ŌĒ	1	Input	Output enable for all channels, active low			
D1	2	Input	Input for channel 1			
D2	3	Input	Input for channel 2			
D3	4	Input	Input for channel 3			
D4	5	Input	Input for channel 4			
D5	6	Input	Input for channel 5			
D6	7	Input	Input for channel 6			
D7	8	Input	Input for channel 7			
D8	9	Input	Input for channel 8			
GND	10	_	Ground			
LE	11	Input	Latch enable			
Q8	12	Output	Output for channel 8			
Q7	13	Output	Output for channel 7			
Q6	14	Output	Output for channel 6			
Q5	15	Output	Output for channel 5			
Q4	16	Output	Output for channel 4			
Q3	17	Output	Output for channel 3			
Q2	18	Output	Output for channel 2			
Q1	19	Output	Output for channel 1			
V <sub>CC</sub>	20	_	Postive supply			
The	rmal Pad	_	The thermal pad can be connect to GND or left floating. Do not connect to any other signal or supply.			

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage		-0.5	7	V
I <sub>IK</sub>	Input clamp current <sup>(2)</sup>	$V_{I} < 0 \text{ or } V_{I} > V_{CC}$		±20	mA
I <sub>OK</sub>	Output clamp current <sup>(2)</sup>	$V_{O}$ < 0 or $V_{O}$ > $V_{CC}$		±20	mA
Io	Continuous output current	$V_{O} = 0$ to $V_{CC}$		±35	mA
I <sub>CC</sub>	Continuous current through $V_{CC}$ or GND	·		±70	mA
TJ	Junction temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

(1) Stresses beyond those listed under Absolute Maximum Rating may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Condition. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

## 6.2 ESD Ratings

			VALUE	UNIT
	Human-body model (HBM), per ANSI/ESDA/ JEDEC JS-001 <sup>(1)</sup>	±4000	V	
V <sub>(ESD)</sub>	Electrostatic discharge	Charged-device model (CDM), per ANSI/ESDA/ JEDEC JS-002 <sup>(2)</sup>	±1500	v

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

#### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM MAX	UNIT
V <sub>CC</sub>	Supply voltage	2	6	V
VI	Input voltage	0	V <sub>CC</sub>	V
Vo	Output voltage	0	V <sub>CC</sub>	V
T <sub>A</sub>	Ambient temperature	-40	125	°C

#### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		SN74		
		RKS (VQFN)	DGS (VSSOP)	UNIT
		20 PINS	20 PINS	-
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	83.2	130.6	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	82.6	68.7	°C/W
R <sub>θJB</sub>	Junction-to-board thermal resistance	57.4	85.4	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	14.5	10.5	°C/W
$\Psi_{JB}$	Junction-to-board characterization parameter	56.4	85.0	°C/W
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	40.0	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.



### **6.5 Electrical Characteristics**

over operating free-air temperature range; typical values measured at  $T_A = 25^{\circ}C$  (unless otherwise noted).

	PARAMETER	TEST CC	NDITIONS	V <sub>cc</sub>	MIN	TYP	MAX	UNIT
				2 V	0.7		1.5	
$V_{T+}$	Positive switching threshold			4.5 V	1.7		3.15	V
				6 V	2.1		4.2	
				2 V	0.3		1	
V <sub>T-</sub>	Negative switching threshold			4.5 V	0.9		2.2	V
				6 V	1.2		3	
ΔV <sub>T</sub>				2 V	0.2		1	
	$V_{T}$ Hysteresis ( $V_{T+} - V_{T-}$ )			4.5 V	0.4		1.4	V
				6 V	0.6		1.6	
			I <sub>OH</sub> = -20 μA	2 V to 6 V	V <sub>CC</sub> – 0.1	$V_{CC} - 0.002$		
V <sub>OH</sub>	High-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$	I <sub>OH</sub> = -6 mA	4.5 V	4	4.3		V
			I <sub>OH</sub> = -7.8 mA	6 V	5.4	5.75		
			I <sub>OL</sub> = 20 μA	2 V to 6 V		0.002	0.1	
V <sub>OL</sub>	Low-level output voltage	$V_{I} = V_{IH} \text{ or } V_{IL}$	I <sub>OL</sub> = 6 mA	4.5 V		0.18	0.3	V
			I <sub>OL</sub> = 7.8 mA	6 V		0.22	0.33	
l <sub>l</sub>	Input leakage current	$V_{I} = V_{CC} \text{ or } 0$	1	6 V		±100	±1000	nA
I <sub>CC</sub>	Supply current	$V_{I} = V_{CC} \text{ or } 0, I_{C}$	<sub>D</sub> = 0	6 V		0.1	2	μA
Ci	Input capacitance			2 V to 6 V			5	pF

## 6.6 Timing Characteristics

over operating free-air temperature range (unless otherwise noted),  $C_L$  = 50 pF

	PARAMETER	CONDITION	V <sub>cc</sub>	MIN MAX	UNIT
			2 V	12	ns
t <sub>w</sub>	Pulse duration	LE high	4.5 V	6	ns
			6 V	6	ns
	Setup time	Data before LE↓	2 V	18	ns
t <sub>su</sub>			4.5 V	6	ns
			6 V	6	ns
			2 V	0	ns
t <sub>h</sub>	Hold time, Data before LE↓		4.5 V	0	ns
			6 V	0	ns

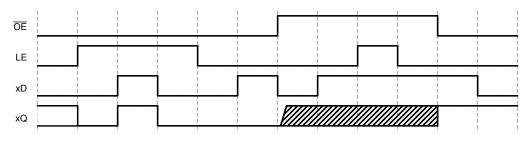


Figure 6-1. Timing diagram



## 6.7 Switching Characteristics

over operating free-air temperature range; typical values measured at  $T_A = 25^{\circ}C$  (unless otherwise noted). See *Parameter Measurement Information*.  $C_L = 50 \text{ pF}$ .

PARAMETER		FROM (INPUT)	TO (OUTPUT)	V <sub>cc</sub>	MIN TYP	MAX	UNIT
				2 V	14.6	19.4	
tt	Transition-time		Any Q	4.5 V	7.7	9.6	ns
				6 V	7.4	10.4	
			Q	2 V	24.5	33	
		D		4.5 V	9.9	14	ns
	Propogation delay			6 V	9.6	11	
t <sub>pd</sub>		LE	Any Q	2 V	24.5	33	
				4.5 V	9.9	14	
				6 V	9.6	11	
		ŌE		2 V	15	44	ns
t <sub>en</sub>	Enable time		Any Q	4.5 V	7	22	
				6 V	6	18	
		OE	Any Q	2 V	12	30	
t <sub>dis</sub>	Disable time		Any Q	4.5 V	9	20	ns
			Any Q	6 V	8	19	

#### 6.8 Operating Characteristics

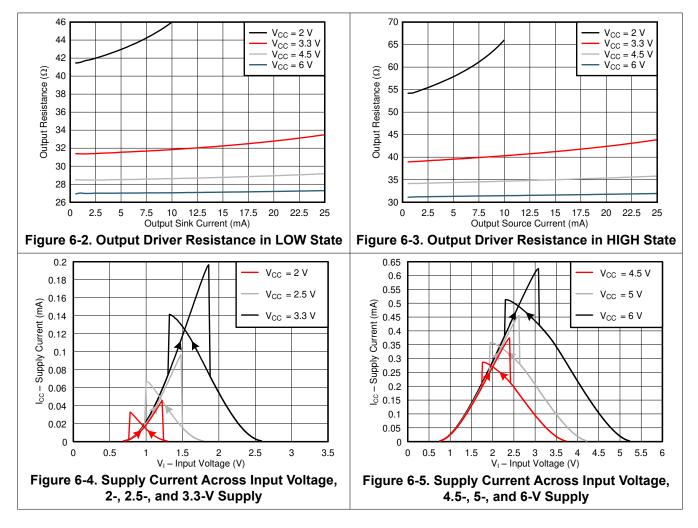
over operating free-air temperature range; typical values measured at T<sub>A</sub> = 25°C (unless otherwise noted).

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
C <sub>pd</sub>	Power dissipation capacitance per gate	No load		20		pF



### **6.9 Typical Characteristics**





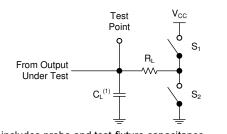


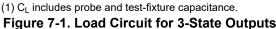
## 7 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  1 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>t</sub> < 2.5 ns.

For clock inputs, f<sub>max</sub> is measured when the input duty cycle is 50%.

The outputs are measured one at a time with one input transition per measurement.





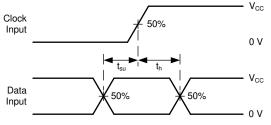
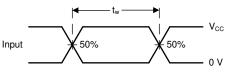
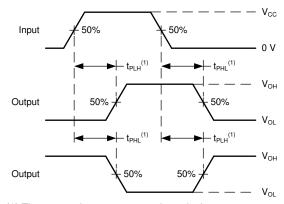
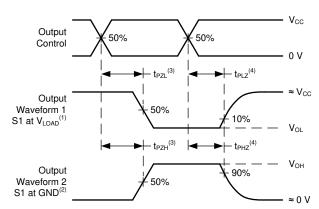


Figure 7-3. Voltage Waveforms, Setup and Hold Times



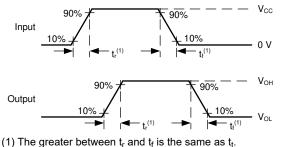


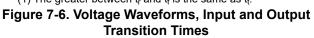






(1) The greater between t<sub>PLH</sub> and t<sub>PHL</sub> is the same as t<sub>pd</sub>. **Figure 7-4. Voltage Waveforms Propagation Delays** 







## 8 Detailed Description

### 8.1 Overview

The SN74HCS573 contains eight D-type latches. All inputs include Schmitt-trigger architecture. All channels share a latch enable (LE) and output enable ( $\overline{OE}$ ) input.

When the latch is enabled (LE is high), data is allowed to pass through from the D inputs to the Q outputs.

When the latch is disabled (LE is low), the Q outputs hold the last state they had regardless of changes at the D inputs.

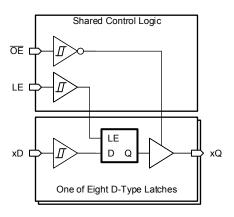
If the latch enable (LE) input is held low during startup, the output state of all channels is unknown until the latch enable (LE) input is driven high with valid input signals at all data (D) inputs.

When the outputs are enabled ( $\overline{OE}$  is low), the outputs are actively driving low or high.

When the outputs are disabled ( $\overline{OE}$  is high), the outputs are set into the high-impedance state.

The active low output enable  $(\overline{OE})$  does not have any impact on the stored state in the latches.

### 8.2 Functional Block Diagram



## 8.3 Feature Description

#### 8.3.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-State outputs. The three states that these outputs can be in are driving high, driving low, and high impedance. The term "balanced" indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance mode, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a 10 k $\Omega$  resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.



#### 8.3.2 CMOS Schmitt-Trigger Inputs

This device includes inputs with the Schmitt-trigger architecture. These inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics* table from the input to ground. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings* table, and the maximum input leakage current, given in the *Electrical Characteristics* table, using Ohm's law ( $R = V \div I$ ).

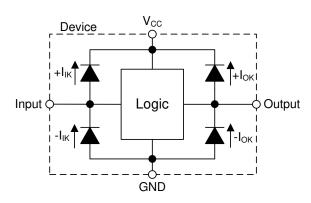
The Schmitt-trigger input architecture provides hysteresis as defined by  $\Delta V_T$  in the *Electrical Characteristics* table, which makes this device extremely tolerant to slow or noisy inputs. While the inputs can be driven much slower than standard CMOS inputs, it is still recommended to properly terminate unused inputs. Driving the inputs with slow transitioning signals will increase dynamic current consumption of the device. For additional information regarding Schmitt-trigger inputs, please see Understanding Schmitt Triggers.

#### 8.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in Electrical Placement of Clamping Diodes for Each Input and Output.

#### CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.



#### Figure 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

#### 8.4 Device Functional Modes

## Table 8-1. Function Table

	OUTPUT <sup>(2)</sup>		
ŌE	LE	D	Q
L	Н	L	L
L	Н	Н	Н
L	L	Х	Q <sub>0</sub> <sup>(3)</sup>
Н	Х	Х	Z

 L = input low, H = input high, ↑ = input transitioning from low to high, ↓ = input transitioning from high to low, X = don't care

(2) L = output low, H = output high, Q<sub>0</sub> = previous state, Z = high impedance

<sup>(3)</sup> At startup, Q<sub>0</sub> is unknown



## 9 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

### 9.1 Application Information

In this application, the SN74HCS573 is used to control an 8-bit data bus.

Outputs can be held in the high-impedance state, held in the last known state, or change together with the data inputs, depending on the control inputs at LE and  $\overline{OE}$  coming from the bus controller.

#### 9.2 Typical Application

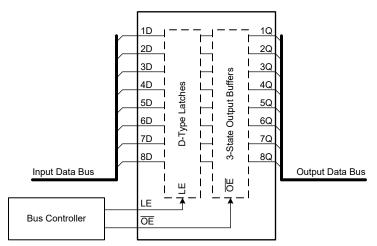


Figure 9-1. Typical application block diagram

#### 9.2.1 Design Requirements



#### 9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the *Recommended Operating Conditions*. The supply voltage sets the device's electrical characteristics as described in the *Electrical Characteristics* section.

The positive voltage supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74HCS573 plus the maximum static supply current,  $I_{CC}$ , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only source as much current that is provided by the positive supply source. Be sure to not exceed the maximum total current through V<sub>CC</sub> listed in the *Absolute Maximum Ratings*.

The ground must be capable of sinking current equal to the total current to be sunk by all outputs of the SN74HCS573 plus the maximum supply current,  $I_{CC}$ , listed in the *Electrical Characteristics*, and any transient current required for switching. The logic device can only sink as much current that can be sunk into its ground connection. Be sure to not exceed the maximum total current through GND listed in the *Absolute Maximum Ratings*.

The SN74HCS573 can drive a load with a total capacitance less than or equal to 50 pF while still meeting all of the data sheet specifications. Larger capacitive loads can be applied; however, it is not recommended to exceed 50 pF.

The SN74HCS573 can drive a load with total resistance described by  $R_L \ge V_O / I_O$ , with the output voltage and current defined in the *Electrical Characteristics* table with  $V_{OH}$  and  $V_{OL}$ . When outputting in the HIGH state, the output voltage in the equation is defined as the difference between the measured output voltage and the supply voltage at the V<sub>CC</sub> pin.

Total power consumption can be calculated using the information provided in *CMOS Power Consumption and Cpd Calculation*.

Thermal increase can be calculated using the information provided in *Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices*.

#### CAUTION

The maximum junction temperature,  $T_{J(max)}$  listed in the *Absolute Maximum Ratings*, is an additional limitation to prevent damage to the device. Do not violate any values listed in the *Absolute Maximum Ratings*. These limits are provided to prevent damage to the device.

#### 9.2.1.2 Input Considerations

Input signals must cross  $V_{t-(min)}$  to be considered a logic LOW, and  $V_{t+(max)}$  to be considered a logic HIGH. Do not exceed the maximum input voltage range found in the *Absolute Maximum Ratings*.

Unused inputs must be terminated to either  $V_{CC}$  or ground. The unused inputs can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input will be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The drive current of the controller, leakage current into the SN74HCS573 (as specified in the *Electrical Characteristics*), and the desired input transition rate limits the resistor size. A 10-k $\Omega$  resistor value is often used due to these factors.

The SN74HCS573 has no input signal transition rate requirements because it has Schmitt-trigger inputs.

Another benefit to having Schmitt-trigger inputs is the ability to reject noise. Noise with a large enough amplitude can still cause issues. To know how much noise is too much, please refer to the  $\Delta V_{T(min)}$  in the *Electrical Characteristics*. This hysteresis value will provide the peak-to-peak limit.

Unlike what happens with standard CMOS inputs, Schmitt-trigger inputs can be held at any valid value without causing huge increases in power consumption. The typical additional current caused by holding an input at a value other than  $V_{CC}$  or ground is plotted in the *Typical Characteristics*.

Refer to the *Feature Description* section for additional information regarding the inputs for this device.



#### 9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the  $V_{OH}$  specification in the *Electrical Characteristics*. The ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the  $V_{OL}$  specification in the *Electrical Characteristics*.

Push-pull outputs that could be in opposite states, even for a very short time period, should never be connected directly together. This can cause excessive current and damage to the device.

Two channels within the same device with the same input signals can be connected in parallel for additional output drive strength.

Unused outputs can be left floating. Do not connect outputs directly to V<sub>CC</sub> or ground.

Refer to the Feature Description section for additional information regarding the outputs for this device.

#### 9.2.2 Detailed Design Procedure

- Add a decoupling capacitor from V<sub>CC</sub> to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V<sub>CC</sub> and GND pins. An example layout is shown in the *Layout* section.
- Ensure the capacitive load at the output is ≤ 50 pF. This is not a hard limit; it will, however, ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HCS573 to one or more of the receiving devices.
- Ensure the resistive load at the output is larger than (V<sub>CC</sub> / I<sub>O(max)</sub>) Ω. This will ensure that the maximum output current from the *Absolute Maximum Ratings* is not violated. Most CMOS inputs have a resistive load measured in MΩ; much larger than the minimum calculated previously.
- 4. Thermal issues are rarely a concern for logic gates; the power consumption and thermal increase, however, can be calculated using the steps provided in the application report, *CMOS Power Consumption and Cpd Calculation*.

#### 9.2.3 Application Curve

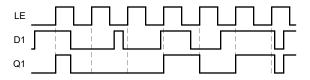


Figure 9-2. Example timing diagram for one channel



## **10 Power Supply Recommendations**

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Recommended Operating Conditions*. Each  $V_{CC}$  terminal should have a good bypass capacitor to prevent power disturbance. A 0.1-µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in given example layout image.

## 11 Layout

### 11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or  $V_{CC}$ , whichever makes more sense for the logic function or is more convenient.

### 11.2 Layout Example

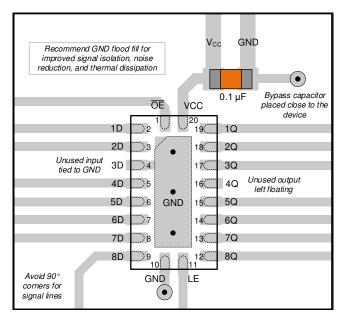


Figure 11-1. Example layout for the SN74HCS573 in the RKS Package



## **12 Device and Documentation Support**

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

#### **12.1 Documentation Support**

#### 12.1.1 Related Documentation

For related documentation see the following:

- Texas Instruments, HCMOS Design Considerations application report (SCLA007)
- Texas Instruments, CMOS Power Consumption and Cpd Calculation application report (SDYA009)
- Texas Instruments, Designing With Logic application report

#### **12.2 Receiving Notification of Documentation Updates**

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### **12.3 Support Resources**

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 12.4 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments.

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#### **12.5 Electrostatic Discharge Caution**



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 12.6 Glossary

TI Glossary This glossary lists and explains terms, acronyms, and definitions.



## 13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.



## PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
SN74HCS573DGSR	ACTIVE	VSSOP	DGS	20	5000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HS573	Samples
SN74HCS573RKSR	ACTIVE	VQFN	RKS	20	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	HCS573	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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#### OTHER QUALIFIED VERSIONS OF SN74HCS573 :

• Automotive : SN74HCS573-Q1

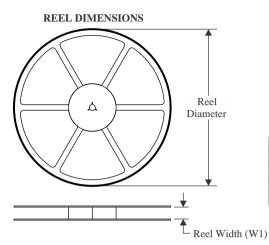
NOTE: Qualified Version Definitions:

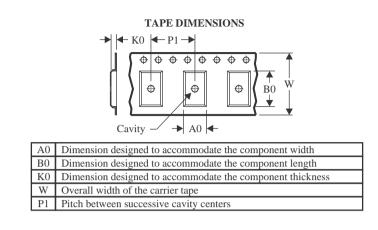
• Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects



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## TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	-	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HCS573DGSR	VSSOP	DGS	20	5000	330.0	16.4	5.4	5.4	1.45	8.0	16.0	Q1
SN74HCS573RKSR	VQFN	RKS	20	3000	180.0	12.4	2.8	4.8	1.2	4.0	12.0	Q1



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# PACKAGE MATERIALS INFORMATION

17-Apr-2023



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HCS573DGSR	VSSOP	DGS	20	5000	356.0	356.0	35.0
SN74HCS573RKSR	VQFN	RKS	20	3000	210.0	185.0	35.0

# **RKS 20**

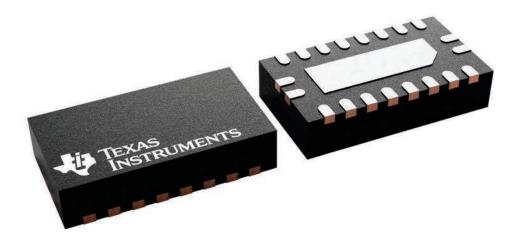
2.5 x 4.5, 0.5 mm pitch

# **GENERIC PACKAGE VIEW**

## VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.





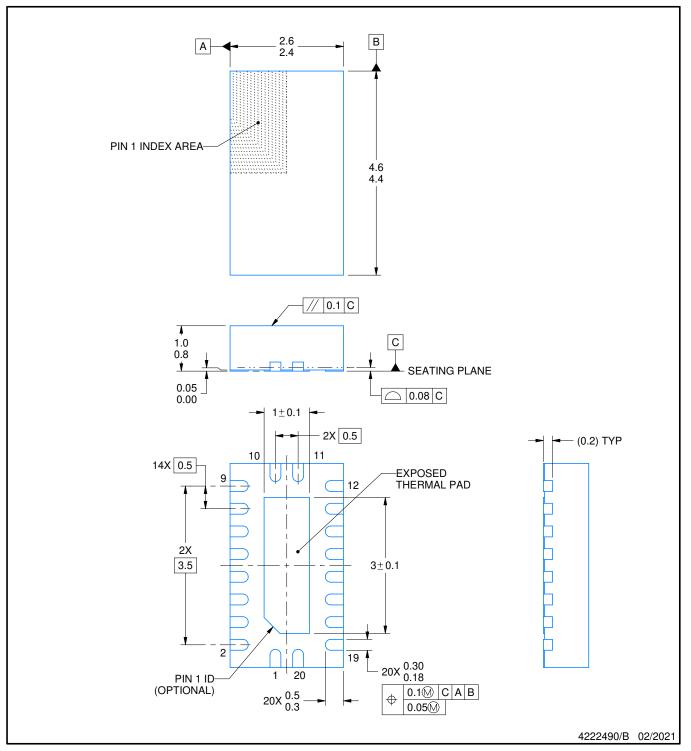
# **RKS0020A**



# **PACKAGE OUTLINE**

## VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M. 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.

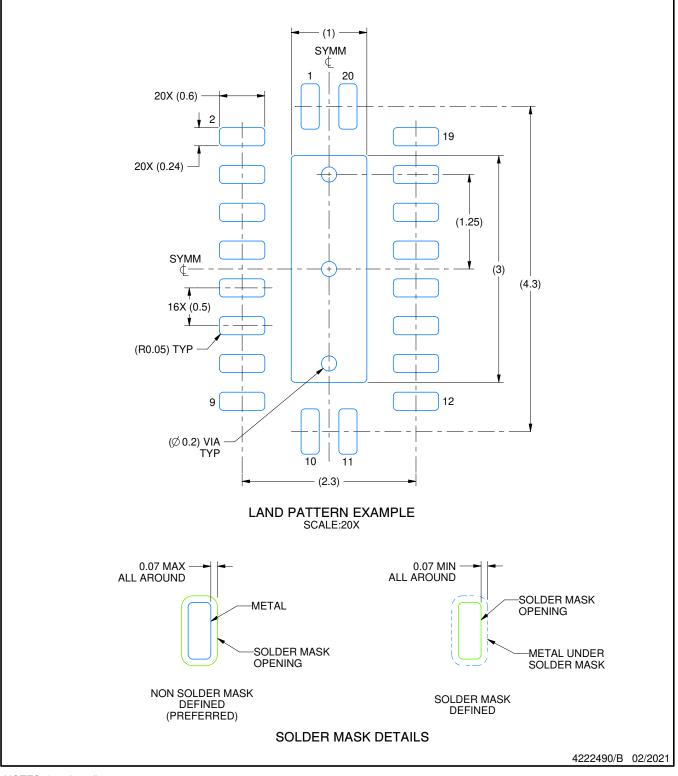


# **RKS0020A**

# **EXAMPLE BOARD LAYOUT**

# VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).

5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.

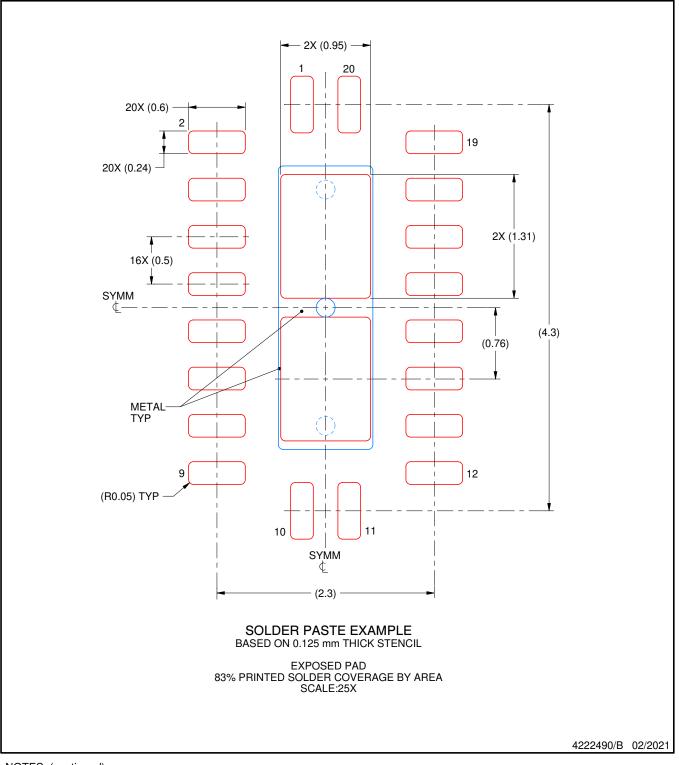


# **RKS0020A**

# **EXAMPLE STENCIL DESIGN**

# VQFN - 1 mm max height

PLASTIC QUAD FLATPACK - NO LEAD



NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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